

### **Amendments to the Specification**

***Please replace the paragraph beginning on page 1, line 10 with the following amended paragraph:***

This application claims priority under 35 U.S.C. 119 to ~~is a counterpart~~ application of Japanese Application Serial Number 246268/2001, filed May 29, 2001, the subject matter of which is incorporated herein by reference.

***Please replace the paragraph beginning on page 11, line 8 with the following amended paragraph:***

FIG. 1 is a block diagram showing a computer for simulation and data to be inputted into the computer according to the present invention, and FIG. 2 is an explanatory view of the method for modeling the semiconductor device process according to the first embodiment. As shown in FIG. 1 Fig. 2, a gate 112 is formed on an upper SiO<sub>2</sub> layer 110 of a semiconductor element 100 via an interface of Si and SiO<sub>2</sub> 130, and a drain 126 is formed on a lower Si layer 120. An S/D profile position 132 changes with conditions of implantation, and the like.